

a homogeneous semiconductor substrate having a first conductivity type;
and

twin wells formed in adjacent regions of a surface portion of said semiconductor substrate,

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a first of the twin wells having a second conductivity type formed in a first portion of the semiconductor substrate such that, in a direction of depth, a junction exists between the first twin well and said semiconductor substrate,
and

a second of the twin wells having the first conductivity type formed in a second portion of the semiconductor substrate such that, in a direction of depth, a junction exists between the second twin well and said semiconductor substrate, wherein said substrate has no buried implanted layer beneath the twin wells, and said first and second wells have a substantially uniform junction depth at substantially all points where said junction exists.

2. (Amended) The semiconductor device as claimed in claim 1, wherein the first and second wells have a substantially uniform junction depth of 1.5 μm .
